L	Hits	Search Text	DB	Time stamp
Number				_
1	102564	DRAM or (dynamic adj5 random adj5 access adj5 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/01 02:35
2	9980	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/01 02:59
3	7163	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:06
5	85	(((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:41
7	59	((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:11
8	38	((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and 365/201.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/01 03:11
10	10	(((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/01 03:16
11	16	365/201.ccls.) and resistanc\$2 (DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:36
12		((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)) and (buried adj3 strap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:19
13	5	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)) and buried	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:35
14	49	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:37
15	10	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/01 03:40
16	1	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried) and 365/199.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:39

18	6	((DRAM or (dynamic adj5 random adj5	USPAT;	2004/10/01
10		access adj5 memory)) and resistance and	US-PGPUB;	03:40
ļ		(selection adj3 transistor) and (storage	EPO; JPO;	03.40
		adj3 capacitor) and buried) and	DERWENT;	i
		365/149.ccls.	IBM TDB	
19	9		USPAT;	2004/10/01
19	9	0420320	US-PGPUB;	03:41
				03:41
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	0004/20/02
20	15	rosskopf-valentin.in.	USPAT;	2004/10/01
			US-PGPUB;	03:41
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
21	2	rosskopf-valentin-\$.in.	USPAT;	2004/10/01
			US-PGPUB;	03:41
			EPO; JPO;	·
		,	DERWENT;	
			IBM TDB	
22	8	felber-andreas.in.	USPAT;	2004/10/01
			US-PGPUB;	03:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
23	0	felber-andreas-\$.in.	USPAT;	2004/10/01
		·	US-PGPUB;	03:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
24	2	sukman-sibina.in.	USPAT;	2004/10/01
			US-PGPUB;	03:42
			EPO; JPO;	
		·	DERWENT;	
			IBM TDB	
25	0	sukman-sibina-\$.in.	USPĀT;	2004/10/01
		7,441	US-PGPUB;	03:42
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
			1 1 1 1 1 1 1 1 1 1	I